

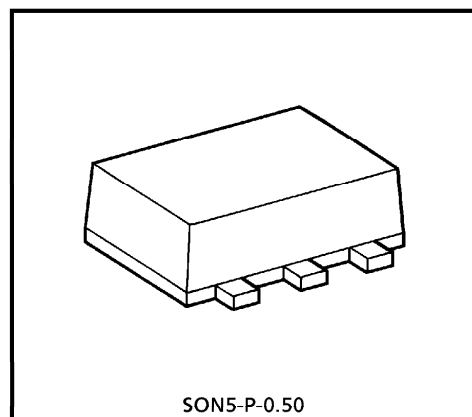
TENTATIVE (UNDER DEVELOPMENT) TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7SZ00AFE

2 INPUT NAND GATE

FEATURES

- High Output Drive : ± 24 mA (Typ.)
@ $V_{CC} = 3$ V
- Super High Speed Operation : $t_{pD} 2.4$ ns (Typ.)
@ $V_{CC} = 5$ V, 50 pF
- Operation Voltage Range : $V_{CC} (opr) = 1.8 \sim 5.5$ V
- Supply Voltage Data Retention : $V_{CC} = 1.5 \sim 5.5$ V
- Latch-up Performance : ± 500 mA
- ESD Performance : Human Body Model $> \pm 2000$ V
Machine Model $> \pm 200$ V
- Power Down Protection is provided on all inputs.
- Matches the Performance of TC74LCX Series when Operated at 3.3 V V_{CC}
- Input Rise and Fall Time (t_r , t_f) (Recommended Operation Condition)
 - @ $V_{CC} = 1.8$ V, 2.5 V ± 0.2 V : 0~20 ns/V
 - @ $V_{CC} = 3.3$ V ± 0.3 V : 0~10 ns/V
 - @ $V_{CC} = 5.5$ V ± 0.5 V : 0~5 ns/V



SON5-P-0.50
Weight : 0.003 g (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V_{CC}	-0.5~6	V
DC Input Voltage	V_{IN}	-0.5~6	V
DC Output Voltage	V_{OUT}	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 50	mA
DC V_{CC} / Ground Current	I_{CC}	± 50	mA
Power Dissipation	P_D	150	mW
Storage Temperature	T_{stg}	-65~150	°C
Lead Temperature (10 s)	T_L	260	°C

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DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION		V _{CC} (V)	Ta = 25°C			Ta = -40~85°C		UNIT	
					MIN.	TYP.	MAX.	MIN.	MAX.		
High-Level Input Voltage	V _{IH}			1.8	0.75 × V _{CC}	—	—	0.75 × V _{CC}	—	V	
				2.3 – 5.5	0.7 × V _{CC}	—	—	0.7 × V _{CC}	—		
Low-Level Input Voltage	V _{IL}			1.8	—	—	0.25 × V _{CC}	—	0.25 × V _{CC}	V	
				2.3 – 5.5	—	—	0.3 × V _{CC}	—	0.3 × V _{CC}		
High-Level Output Voltage	V _{OH}	V _{IN} = V _{IH} or V _{IL}		I _{OH} = -100 μA	1.8	1.7	1.8	—	1.7	—	V
					2.3	2.2	2.3	—	2.2	—	
					3.0	2.9	3.0	—	2.9	—	
				I _{OH} = -8 mA	4.5	4.4	4.5	—	4.4	—	
					2.3	1.9	2.15	—	1.9	—	
					3.0	2.4	2.8	—	2.4	—	
					3.0	2.3	2.68	—	2.3	—	
I _{OH} = -32 mA	4.5	3.8	4.2	—	3.8	—					
Low-Level Output Voltage	V _{OL}	V _{IN} = V _{IH}		I _{OL} = 100 μA	1.8	—	0	0.1	—	0.1	V
					2.3	—	0	0.1	—	0.1	
					3.0	—	0	0.1	—	0.1	
					4.5	—	0	0.1	—	0.1	
				I _{OL} = 8 mA	2.3	—	0.1	0.3	—	0.3	
					3.0	—	0.15	0.4	—	0.4	
					3.0	—	0.22	0.55	—	0.55	
I _{OL} = 32 mA	4.5	—	0.22	0.55	—	0.55					
Input Leakage Current	I _{IN}	V _{IN} = 5.5 V or GND		0 – 5.5	—	—	± 1	—	± 10	μA	
Quiescent Supply Current	I _{CC}	V _{IN} = V _{CC} or GND		5.5	—	—	2	—	20	μA	

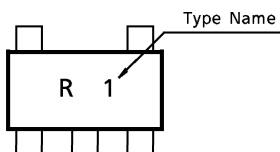
AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3\text{ ns}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	Ta = 25°C			Ta = -40~85°C		UNIT	
			V _{CC} (V)	MIN.	TYP.	MAX.	MIN.		MAX.
Propagation Delay Time	t _{PLH} t _{PHL}	C _L = 15 pF, R _L = 1 MΩ	1.8	2.0	4.5	9.5	2.0	10.0	ns
			2.5 ± 0.2	0.8	3.0	6.5	0.8	7.0	
			3.3 ± 0.3	0.5	2.4	4.5	0.5	4.7	
		5.0 ± 0.5	0.5	2.0	3.9	0.5	4.1		
		C _L = 50 pF, R _L = 500 Ω	3.3 ± 0.3	1.5	2.9	5.0	1.5	5.2	
5.0 ± 0.5	0.8		2.4	4.3	0.8	4.5			
Input Capacitance	C _{IN}		0 - 5.5	—	4	—	—	pF	
Power Dissipation Capacitance	C _{PD}	(Note 1)	3.3	—	19	—	—	—	pF
			5.5	—	27	—	—	—	

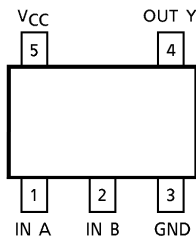
(Note 1) : C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.
Average operating current can be obtained by the equation.

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

MARKING



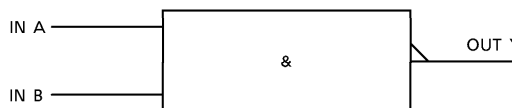
PIN ASSIGNMENT (TOP VIEW)



TRUTH TABLE

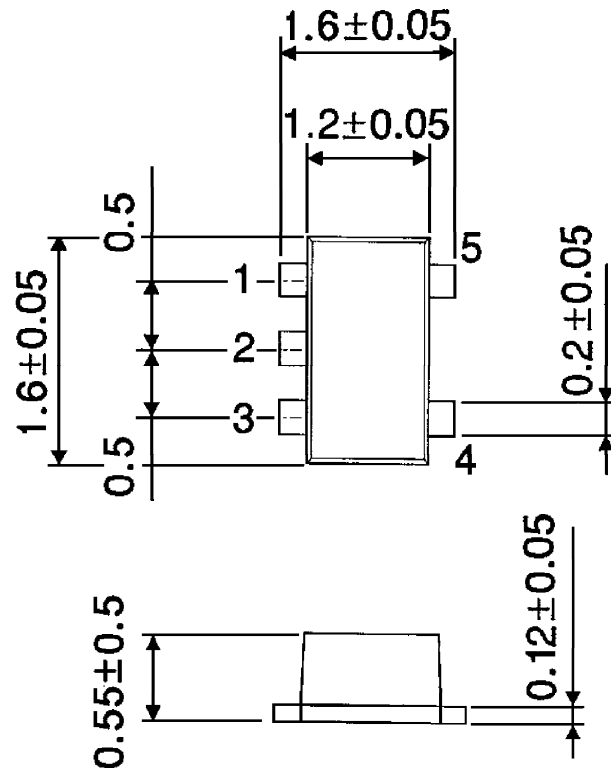
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

LOGIC DIAGRAM



OUTLINE DRAWING
SON5-P-0.50

Unit : mm



Weight : 0.003 g (Typ.)